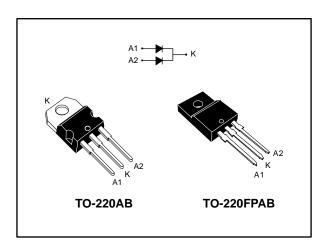


## STPS20SM80C

### Power Schottky rectifier

Datasheet - production data



#### **Features**

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
  - Insulated voltage: 2000 V<sub>RMS</sub> sine

#### **Description**

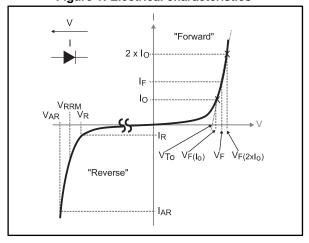
This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB and TO-220FPAB, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

**Table 1: Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	2 x 10 A
V <sub>RRM</sub>	80 V
T <sub>i</sub> (max.)	175 °C
V <sub>F</sub> (typ.)	515 mV

Figure 1: Electrical characteristics



1

 $V_{ARM}$  and  $I_{ARM}$  must respect the reverse safe operating area defined in Figure 10.  $V_{AR}$  and  $I_{AR}$  are pulse measurements ( $t_p < 1 \ \mu s$ ).  $V_R$ ,  $I_R$ ,  $V_{RRM}$  and  $V_F$ , are static characteristics.

Characteristics STPS20SM80C

#### 1 Characteristics

Table 2: Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Parameter				Value	Unit	
V <sub>RRM</sub>	Repetitive peak reve	rse voltage			80	V	
I <sub>F(RMS)</sub>	Forward rms current				30	Α	
		TO 00045	T <sub>C</sub> = 155 °C	Per diode	10		
	Average forward	TO-220AB	T <sub>C</sub> = 150 °C	Per device	20		
I <sub>F(AV)</sub>	current δ = 0.5, square wave	TO 000EDAD	T <sub>C</sub> = 130 °C	Per diode	10	A	
		TO-220FPAB	T <sub>C</sub> = 100 °C	Per device	20		
IFSM	Surge non repetitive forward current		t <sub>p</sub> = 10 ms sinusoidal		220	Α	
Parm <sup>(1)</sup>	Repetitive peak avalanche power		$t_p = 10 \ \mu s, \ T_j = 125 \ ^{\circ}C$		385	W	
V <sub>ARM</sub> <sup>(2)</sup>	Maximum repetitive peak avalanche voltage		$t_p < 1 \mu s$ , $T_j < 150 ^{\circ}C$ , $I_{AR} < 16.2 ^{\circ}A$		100	V	
V <sub>ASM</sub> <sup>(2)</sup>	Maximum single pulse peak avalanche voltage		$t_p$ < 1 $\mu$ s, $T_j$ < 150 °C, $I_{AR}$ < 16.2 A		100	V	
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C		
Tj	Maximum operating junction temperature (3)			175	°C		

#### Notes:

**Table 3: Thermal parameters** 

Symbol	Parame	Max. value	Unit			
		TO-220AB	Per diode	2.30		
D. Lunation to some	10-220AB	Total	1.55	0000		
Kth(j-c)	R <sub>th(j-c)</sub> Junction to case	TO-220FPAB	Per diode	5.80	°C/W	
		10-220FPAB	Total	4.65		
R <sub>th(c)</sub> Coupling	TO-220AB		0.80	°C/W		
	Coupling	TO-220FPAB	3.50	C/VV		

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j \; (diode1)} = P_{(diode1)} \; x \; R_{th(j-c)} \; (per \; diode) \; + \; P_{(diode2)} \; x \; R_{th(c)}$$

<sup>&</sup>lt;sup>(1)</sup>For pulse time duration deratings, please refer to figure 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

<sup>(2)</sup>See Figure 10

 $<sup>^{(3)}(</sup>dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

STPS20SM80C Characteristics

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
1 (1)	T <sub>j</sub> = 25 °C	V V	-	5.8	25	μΑ	
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$	-	5	15	mA
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A	-	0.590	0.640	
		T <sub>j</sub> = 125 °C		-	0.515	0.550	
\/_(2)		T <sub>j</sub> = 25 °C		-	0.710	0.780	V
VF(=)		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 10 A	-	0.595	0.650	V
		T <sub>j</sub> = 25 °C	I- 20 A	-	0.850	0.945	
		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 20 A	-	0.690	0.780	

#### Notes:

 $^{(1)}$ Pulse test: t<sub>p</sub> = 5 ms,  $\delta$  < 2%

 $^{(2)} Pulse$  test:  $t_p$  = 380  $\mu s, \, \delta < 2\%$ 

To evaluate the conduction losses, use the following equation:

 $P = 0.52 \text{ x } I_{F(AV)} + 0.013 \text{ x } I_{F^2(RMS)}$ 

Characteristics STPS20SM80C

### 1.1 Characteristics (curves)

Characteristics (curves)

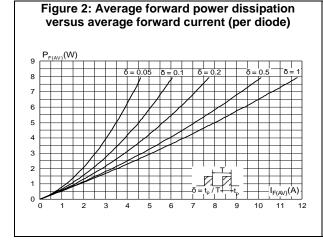


Figure 3: Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

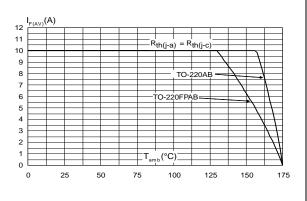


Figure 4: Normalized avalanche power derating versus pulse duration ( $T_j = 125$  °C)

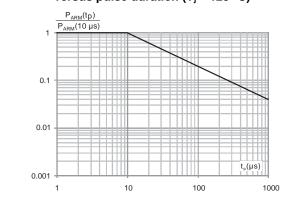


Figure 5: Relative thermal impedance junction to case versus pulse duration (TO-220AB)

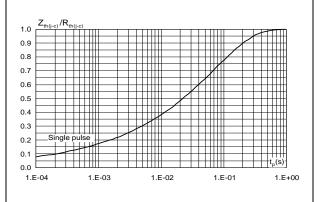


Figure 6: Relative thermal impedance junction to case versus pulse duration (TO-220FPAB)

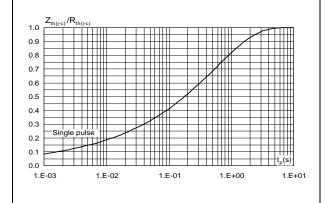
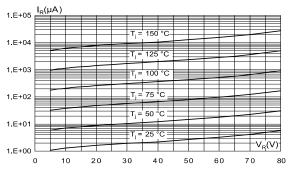


Figure 7: Reverse leakage current versus reverse voltage applied (typical values, per diode)



STPS20SM80C Characteristics

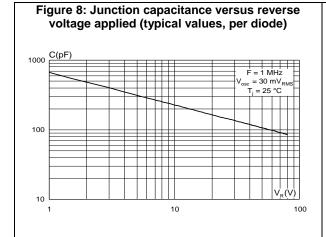
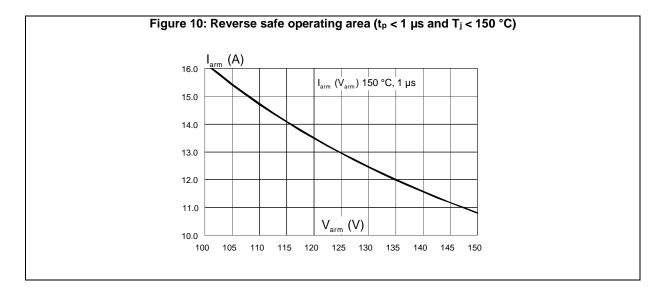


Figure 9: Forward voltage drop versus forward



Package information STPS20SM80C

## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL 94,V0
- Recommended torque value: 0.55 N·m (for TO-220AB and TO-220FPAB)
- Maximum torque value: 0.7 N·m (for TO-220AB and TO-220FPAB)

### 2.1 TO-220AB package information

Figure 11: TO-220AB package outline

Table 5: TO-220AB package mechanical data

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
b	0.61	0.88	0.240	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.028	
D	15.25	15.75	0.600	0.620	
D1	1.27 typ.		0.050	0 typ.	
Е	10.00	10.40	0.394	0.409	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.244	0.260	
J1	2.40	2.72	0.094	0.107	
L	13.00	14.00	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L20	16.40 typ.		0.646 typ.		
L30	28.90 typ.		1.138 typ.		
θР	3.75	3.85	0.148	0.152	
Q	2.65	2.95	0.104	0.116	

Package information STPS20SM80C

## 2.2 TO-220FPAB package information

Figure 12: TO-220FPAB package outline

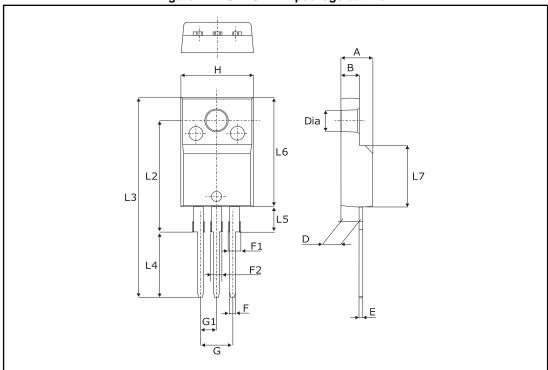


Table 6: TO-220FPAB package mechanical data

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.50	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1.0	0.03	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.40	2.70 0.094		0.106	
Н	10.00	10.40	10.40 0.393		
L2	16.00	0 typ.	0.63 typ.		
L3	28.60	30.60	1.126	1.205	
L4	9.80	10.6	0.386	0.417	
L5	2.90	3.60	0.114	0.142	
L6	15.90	16.40	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia	3.0	3.20	0.118	0.126	

STPS20SM80C Ordering information

# 3 Ordering information

**Table 7: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS20SM80CT	PS20SM80CT	TO-220AB	1.9 g	50	Tube
STPS20SM80CFP	PS20SM80CFP	TO-220FPAB	1.9 g	50	Tube

# 4 Revision history

**Table 8: Document revision history** 

Date	Revision	Changes
11-Apr-2011	1	First issue.
12-May-2017	2	Removed D <sup>2</sup> PAK and DPAK packages.

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